



BSS138DW

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _A = +25°C |
|-------------------|------------------------------|--|
| 50V | 3.5Ω @ V _{GS} = 10V | 200mA |

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch

SOT363 (Standard)



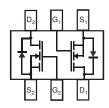
Top View

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at
 - https://www.diodes.com/products/automotive/automotive-products/.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (BSS138DWQ)

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Top View Internal Schematic

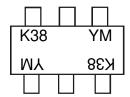
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|--------------|-------------------|------------------|
| BSS138DW-7-F | SOT363 (Standard) | 3000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K38 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

| Year | 2007 | | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 |
|-------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code | U | | I | J | K | L | М | N | 0 | Р | R | S |
| | | | | | | | | | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|-----------------------------|------------------|------------------|------|----|
| Drain-Source Voltage | V _{DSS} | 50 | V | |
| Drain-Gate Voltage (Note 7) | | V_{DGR} | 50 | V |
| Gate-Source Voltage | Continuous | V _{GSS} | ±20 | V |
| Drain Current (Note 5) | Continuous | I _D | 200 | mA |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|--|----------|-------------|------|
| Total Power Dissipation (Note 5) | PD | 200 | mW |
| Thermal Resistance, Junction to Ambient (Note 5) | Reja | 625 | °C/W |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | °C |

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|-----------------------------------|---------------------|-----|-----|------|------|--|
| OFF CHARACTERISTICS (Note 6) | | | | | | |
| Drain-Source Breakdown Voltage | BVDSS | 50 | 75 | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current | IDSS | _ | _ | 0.5 | μΑ | $V_{DS} = 50V$, $V_{GS} = 0V$ |
| Gate-Body Leakage | Igss | _ | _ | ±100 | nΑ | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 6) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.5 | 1.2 | 1.5 | ٧ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | 1.4 | 3.5 | Ω | $V_{GS} = 10V, I_D = 0.22A$ |
| Forward Transconductance | g FS | 100 | _ | _ | mS | $V_{DS} = 25V$, $I_{D} = 0.2A$, $f = 1.0kHz$ |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | Ciss | _ | _ | 50 | рF | |
| Output Capacitance | Coss | | _ | 25 | рF | $V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$ |
| Reverse Transfer Capacitance | Crss | | _ | 8.0 | рF | |
| Turn-On Delay Time | td(ON) | _ | _ | 20 | ns | $V_{DD} = 30V, I_D = 0.2A,$ |
| Turn-Off Delay Time | tD(OFF) | _ | _ | 20 | ns | $R_{GEN} = 50\Omega$ |

5. Device mounted on FR-4 PCB, 1 inch \times 0.85 inch \times 0.062 inch; pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html.

- 6. Short duration pulse test used to minimize self-heating effect.
- 7. $R_{GS} \le 20 k \Omega$. 8. Guaranteed by design. Not subject to product testing.



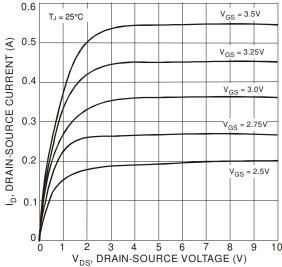


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

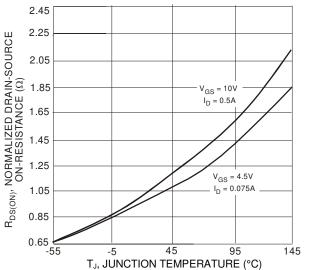


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

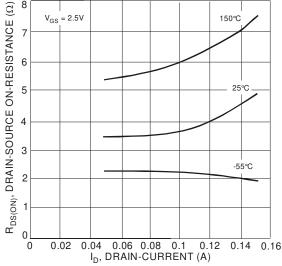
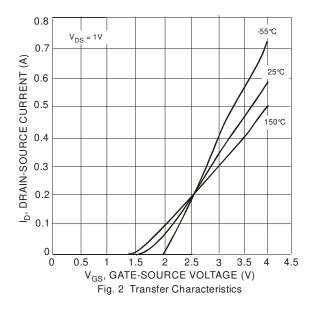


Fig. 5 Drain-Source On-Resistance vs. Drain-Current



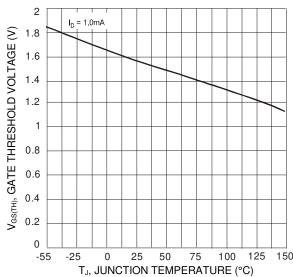


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

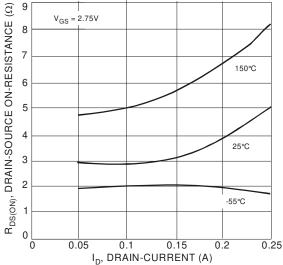
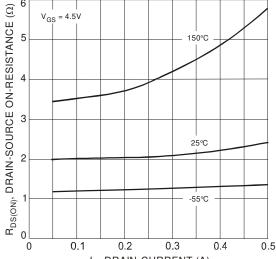
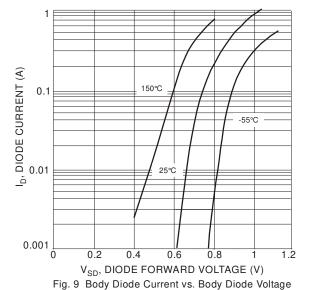


Fig. 6 Drain-Source On-Resistance vs. Drain-Current





 ${\rm I_D}, {\rm DRAIN\text{-}CURRENT}$ (A) Fig. 7 Drain-Source On-Resistance vs. Drain-Current



3.5 150°C $R_{\text{DS(ON)}},$ DRAIN-SOURCE ON-RESISTANCE (Ω) V_{GS} = 10V 2.5 25°C -55°C 0.5 0 0.1 0.2 0.3 0.4 0.5 I_D, DRAIN-CURRENT (A) Fig. 8 Drain-Source On-Resistance vs. Drain-Current

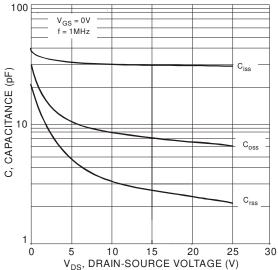
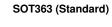


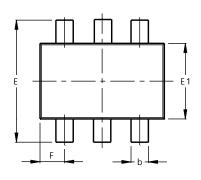
Fig. 10 Capacitance vs. Drain-Source Voltage

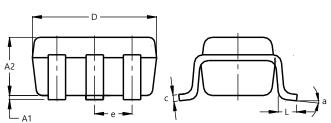


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





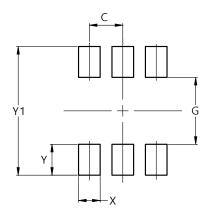


| SOT363 (Standard) | | | | | | | |
|----------------------|------|------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| A1 | 0.00 | 0.10 | 0.05 | | | | |
| A2 | 0.80 | 1.00 | 0.90 | | | | |
| Ь | 0.10 | 0.35 | 0.225 | | | | |
| С | 0.08 | 0.22 | 0.15 | | | | |
| D | 1.80 | 2.20 | 2.00 | | | | |
| Е | 2.00 | 2.45 | 2.225 | | | | |
| E1 | 1.15 | 1.35 | 1.25 | | | | |
| е | | | 0.65 | | | | |
| F | 0.25 | 0.45 | 0.35 | | | | |
| Ĺ | 0.25 | 0.46 | 0.355 | | | | |
| а | 0° | 8° | | | | | |
| All Dimensions in mm | | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363 (Standard)



| Dimensions | Value (in mm) |
|------------|------------------|
| С | 0.650 |
| G | 1.300 |
| X | 0.420 |
| Y | 0.600 |
| Y1 | 2.500 |



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